BUK9J0R9-40H

N-channel 40 V, 0.9 mΩ logic level MOSFET in LFPAK56E

7 October 2019 — Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in an enhanced LFPAK56E package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight $V_{GS(th)}$ limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced R_{th} and R_{DSon}
  - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	220	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	500	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.53	0.82	0.94	mΩ

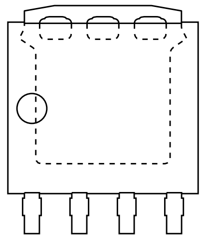
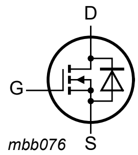
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 20 V; V_{GS} = 4.5 V; Fig. 13; Fig. 14		-	12.7	25.3	nC
Source-drain diode							
Q_r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C	[2]	-	52.6	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 17		-	0.77	-	

[1] 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	**LFPAK56E; Power-SO8 (SOT1023)**	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9J0R9-40H	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9J0R9-40H	90H940E

8. Limiting values

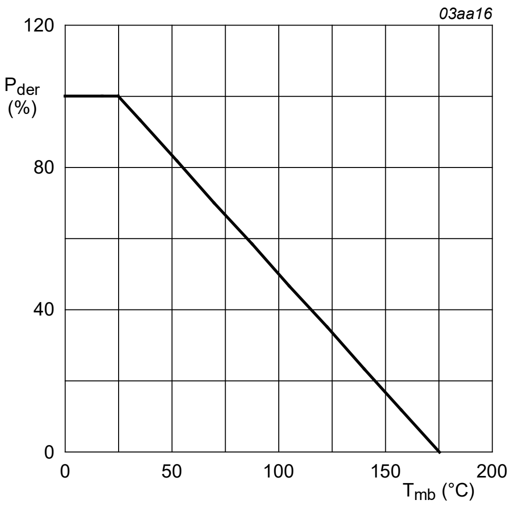
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage	DC; T_j ≤ 175 °C		-10	16	V

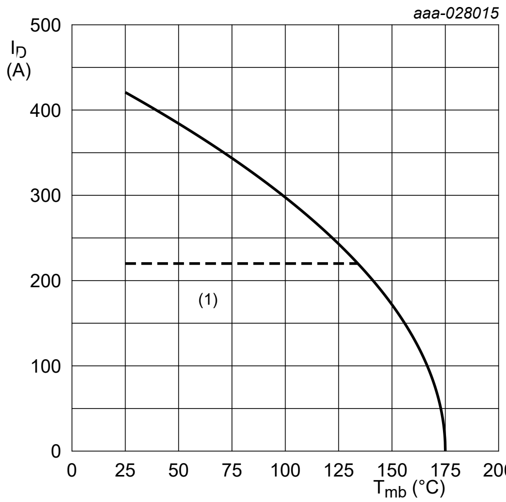
Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	500	W
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	220	A
		V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 2	[1]	-	220	A
I_{DM}	peak drain current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C; Fig. 3		-	600	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[2]	-	165	A
I_{SM}	peak source current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	600	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 160 A; $V_{sup} \leq$ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	290	mJ

[1] 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
[2] 165A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[4] Refer to application note AN10273 for further information.



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

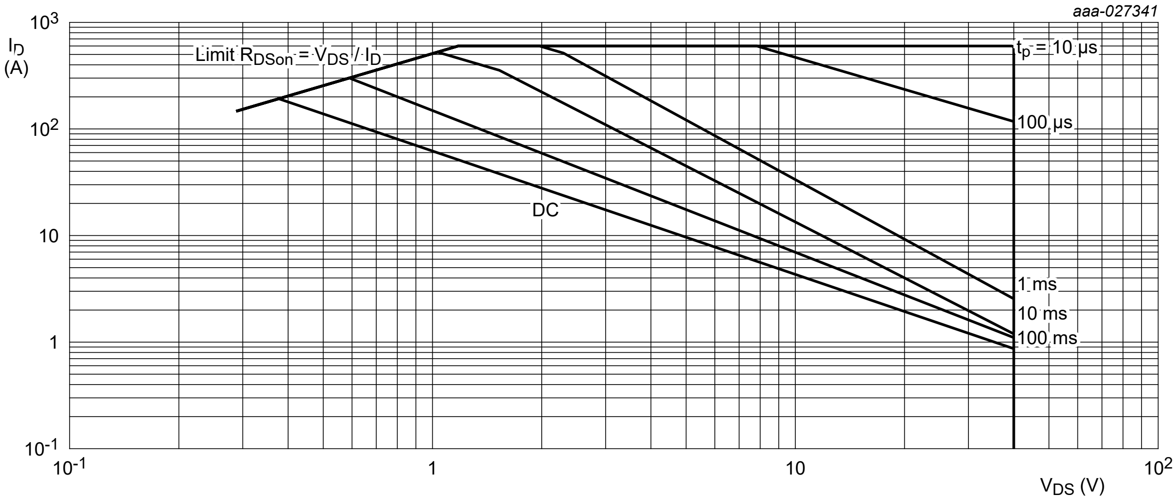
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq$ 10 V

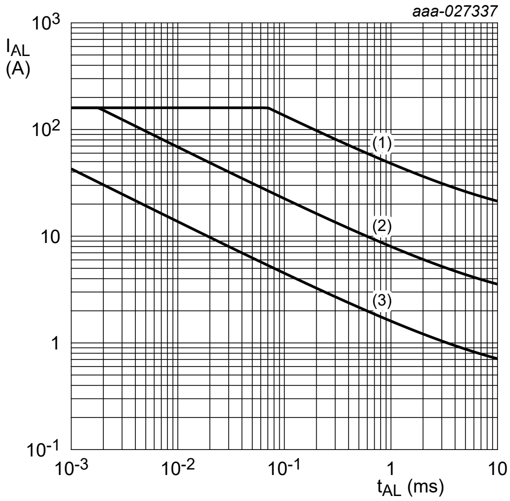
(1) 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j\ (init)}$ = 25 °C; (2) $T_{j\ (init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.21	0.3	K/W

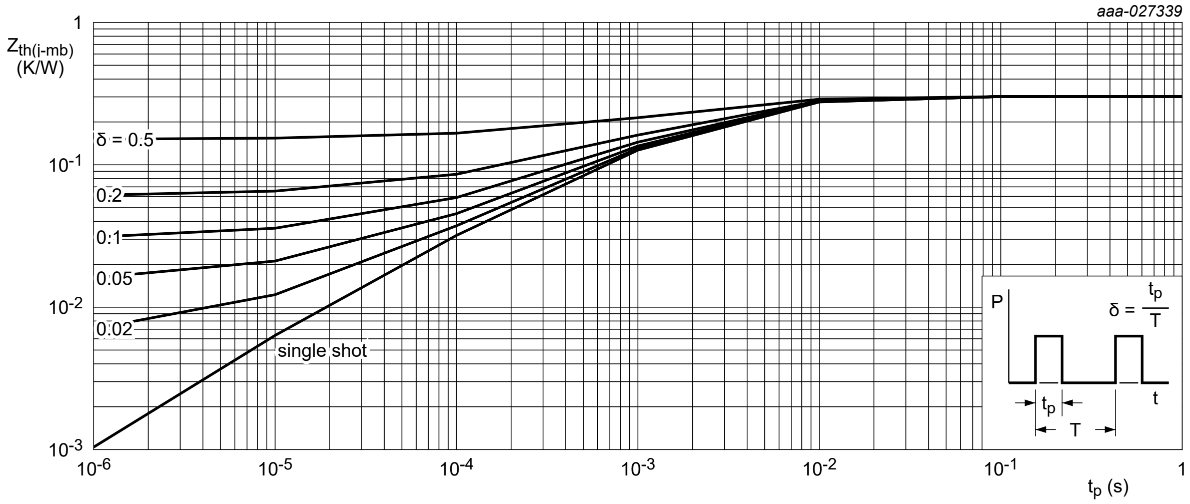


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

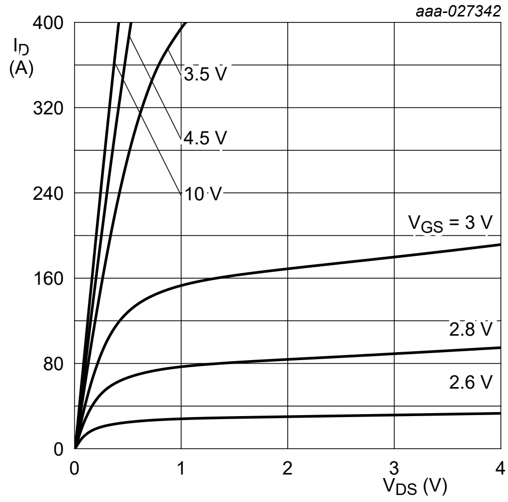
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	43	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -40 °C		-	40.5	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		1.35	1.66	2.05	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 °C; Fig. 10		0.6	-	-	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 °C; Fig. 10		-	-	2.5	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.4	5	µA
		V_{DS} = 16 V; V_{GS} = 0 V; T_j = 125 °C		-	3.2	25	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C		-	405	1000	µA
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA

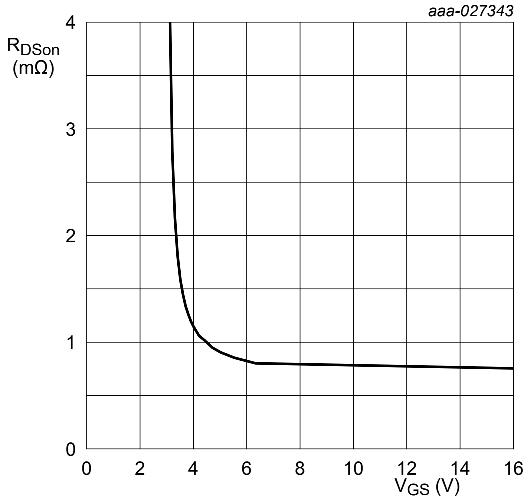
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.53	0.82	0.94	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 105 °C; Fig. 12		0.79	1.17	1.48	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 125 °C; Fig. 12		0.87	1.29	1.64	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12		1.1	1.63	2.05	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.68	0.97	1.2	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 105 °C; Fig. 12		1	1.47	1.9	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 125 °C; Fig. 12		1.1	1.62	2.1	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 175 °C; Fig. 12		1.4	2.03	2.6	mΩ
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		0.42	1.04	2.6	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 20 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	120	168	nC
		I_D = 25 A; V_{DS} = 20 V; V_{GS} = 4.5 V; Fig. 13; Fig. 14		-	54.2	76	nC
Q_{GS}	gate-source charge			-	20.2	30.2	nC
Q_{GD}	gate-drain charge			-	12.7	25.3	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	8977	12568	pF
C_{oss}	output capacitance			-	1549	2168	pF
C_{rss}	reverse transfer capacitance			-	346	760	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 20 V; R_L = 0.8 Ω; V_{GS} = 4.5 V; $R_{G(ext)}$ = 5 Ω		-	45.4	-	ns
t_r	rise time			-	46.2	-	ns
$t_{d(off)}$	turn-off delay time			-	59.2	-	ns
t_f	fall time			-	32.6	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.76	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	44.6	-	ns
Q_r	recovered charge		[1]	-	52.6	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 17		-	0.77	-	
		I_S = 25 A; dI_S/dt = -500 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 17		-	0.67	-	

[1] includes capacitive recovery



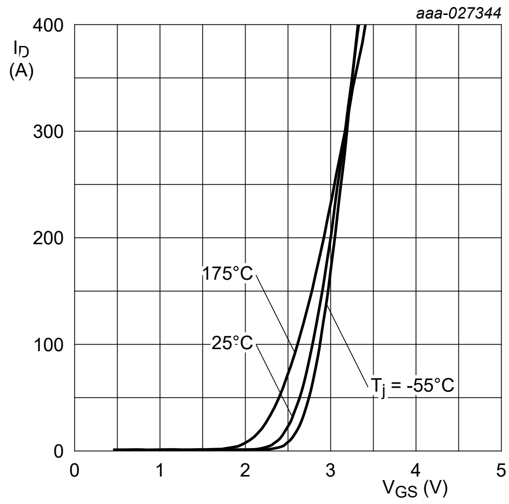
T_j = 25 °C

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



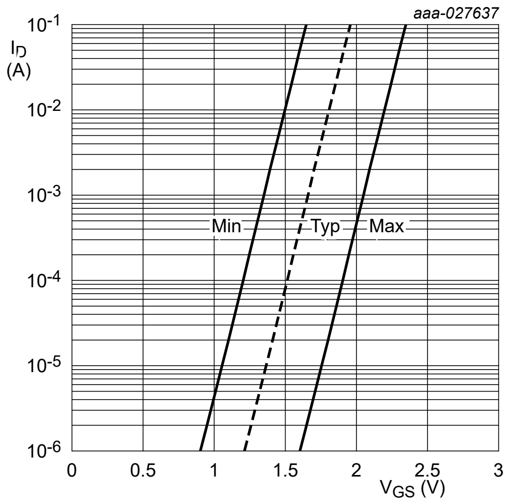
T_j = 25 °C; I_D = 25 A

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



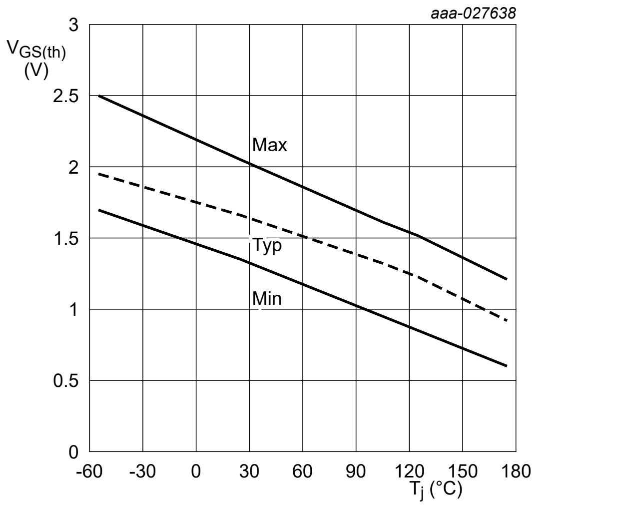
V_{DS} = 8 V

Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



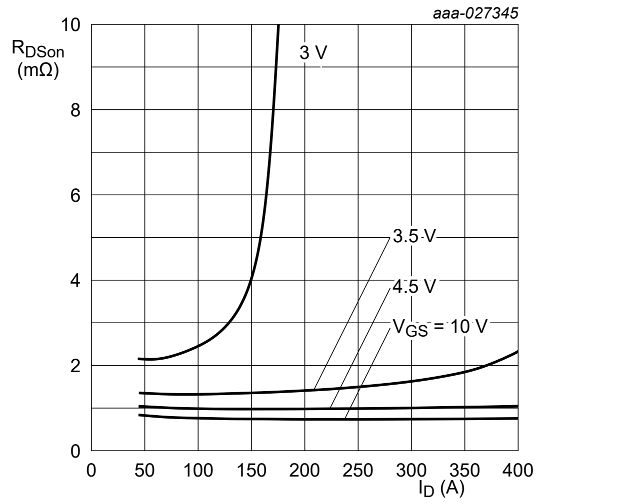
T_j = 25 °C; V_{DS} = 5 V

Fig. 9. Sub-threshold drain current as a function of gate-source voltage



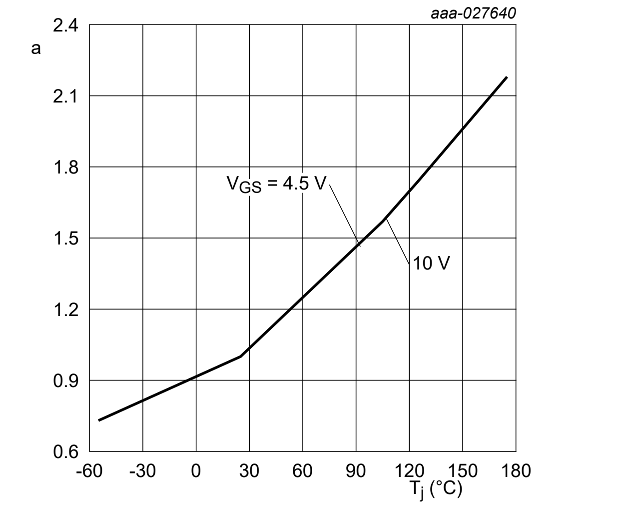
I_D = 1 mA ; V_{DS} = V_{GS}

Fig. 10. Gate-source threshold voltage as a function of junction temperature



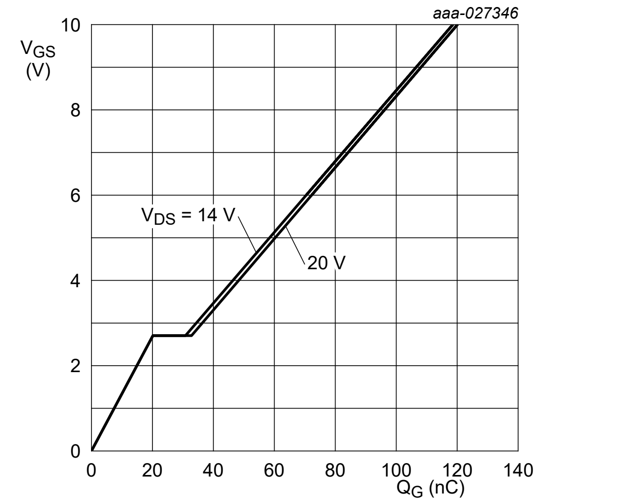
T_j = 25 °C

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 25 A

Fig. 13. Gate-source voltage as a function of gate charge; typical values

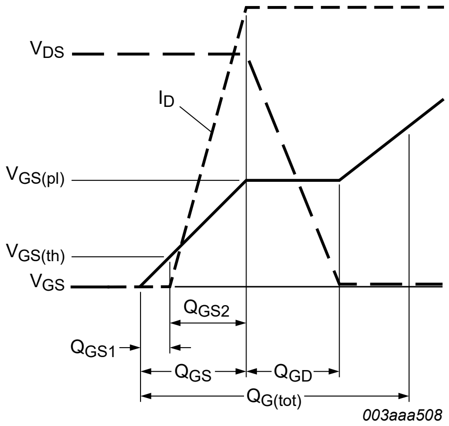
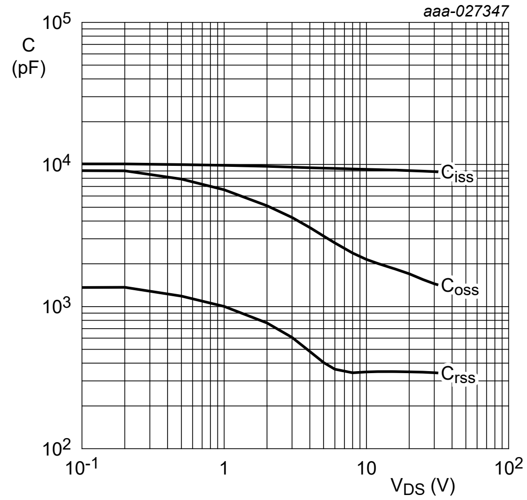
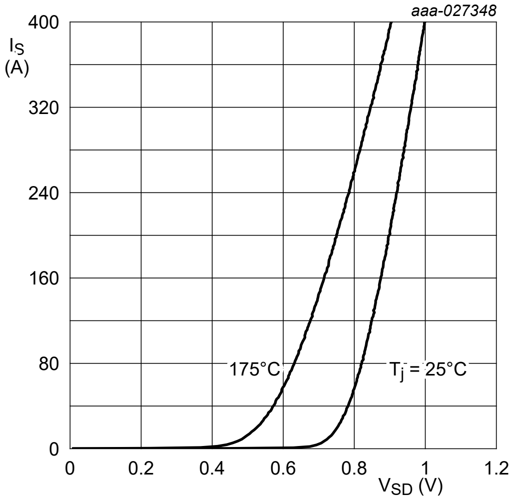


Fig. 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{GS} = 0 V

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

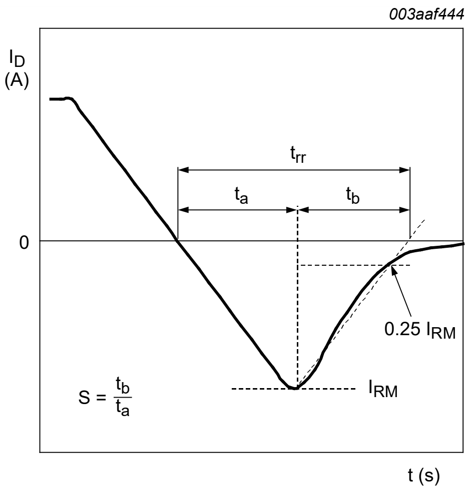
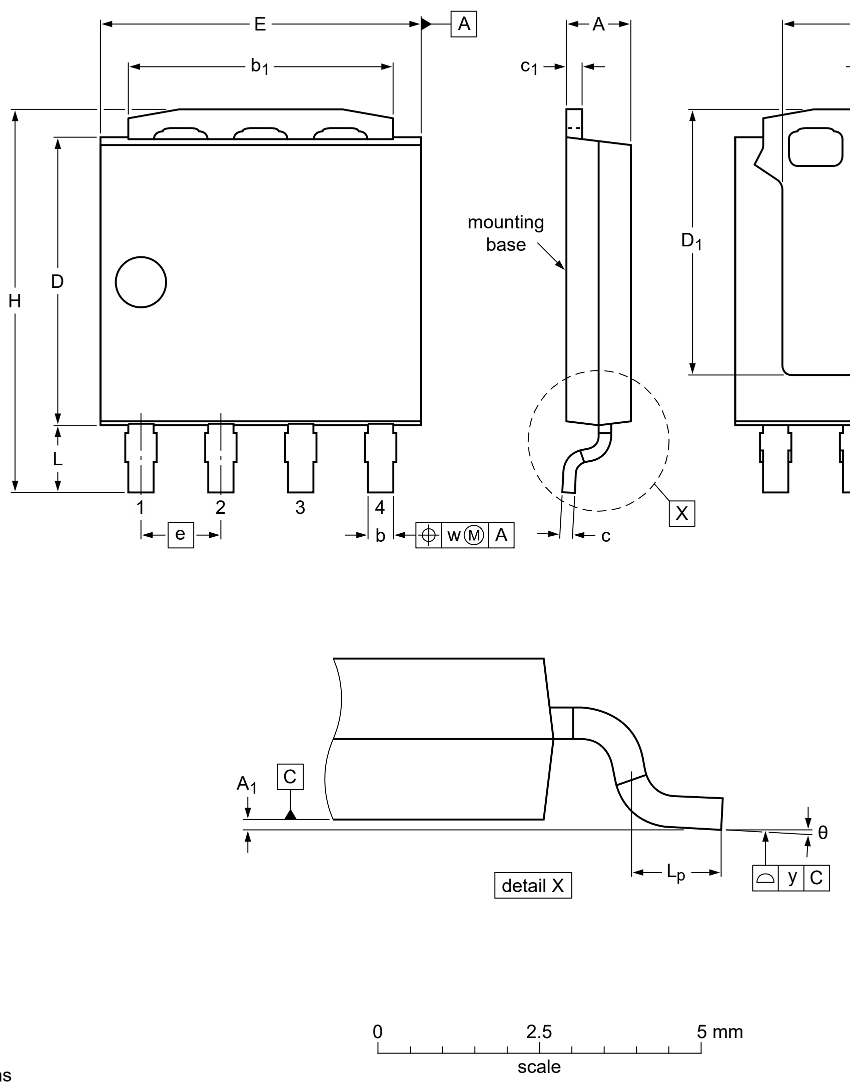


Fig. 17. Reverse recovery timing definition

11. Package outline

Plastic single-ended surface-mounted package (LFPAK56E); 4 leads **SOT1023**



Dimensions

Unit		A	A_1	b	b_1	b_2	c	c_1	D[(1)]	D_1[(1)]	E[(1)]	E_1[(1)]	e	H	L	L_p	w	y	θ
mm	max	1.10	0.15	0.50	4.41		0.25	0.30	4.70	4.45	5.30	3.7		6.2	1.3	0.85			8°
	nom					0.85							1.27				0.25	0.1	
	min	0.95	0.00	0.35	3.62		0.19	0.24	4.45		4.95	3.5		5.9	0.8	0.40			0°

Note

1. Plastic or metal protrusions of 0.15 mm per side are not included.

sot1023_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1023						~~13-03-05~~ 17-07-31

Fig. 18. Package outline LFPAK56E; Power-SO8 (SOT1023)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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